

### Features

- Low ON-state resistance.
- 4V drive.
- Mount height of 1.1mm.
- Complex Type enabling high density mount

TENTATIVE

### Absolute Maximum Ratings / Ta=25°C

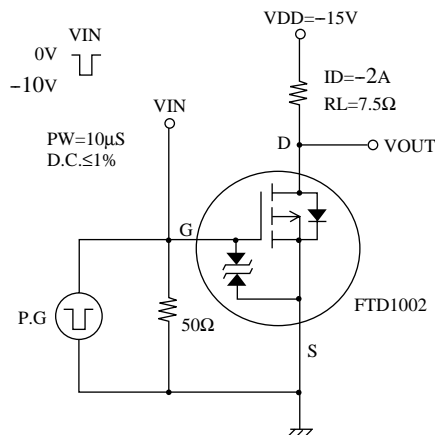
			unit
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current(DC)	ID	-2	A
Drain Current(Pulse)	IDP	PW≤10μS, dutycycle≤1%	-15 A
Allowable power Dissipation	PD	Mounted on ceramic board (1000mm <sup>2</sup> × 0.8mm) 1unit	0.8 W
Total Dissipation	PT	Mounted on ceramic board (1000mm <sup>2</sup> × 0.8mm)	1.0 W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

### Electrical Characteristics / Ta=25°C

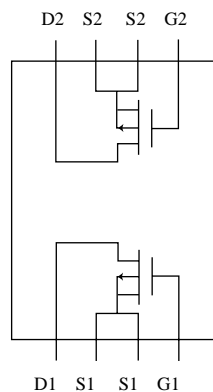
			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0	-30			V
Zero Gate Voltage Drain Current	IDSS	VDS=-30V, VGS=0			-100	μA
Gate to Source Leakage Current	IGSS	VGS=±16V, VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-1		-2.5	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-2A	2.5	3.7		S
Static Drain to Source On State Resistance	RDS(on) 1	ID=-2A, VGS=-10V		90	115	mΩ
	RDS(on) 2	ID=-1A, VGS=-4V		170	240	mΩ
Input Capacitance	Ciss	VDS=-10V, f=1MHz		400		pF
Output Capacitance	Coss	VDS=-10V, f=1MHz		230		pF
Reverse Transfer Capacitance	Crss	VDS=-10V, f=1MHz		110		pF
Turn-ON Delay Time	td(on)	See Specified Test Circuit		10		ns
Rise Time	tr		30	ns		
Turn-OFF Delay Time	td(off)		55	ns		
Fall Time	tf		50	ns		
Total Gate Charge	Qg		VDS=-10V, VGS=-10V, ID=-2A		14	
Gate Source Charge	Qgs	1.5		nC		
Gate Drain Charge	Qgd	4.7		nC		
Diode Forward Voltage	VSD	IS=-2A, VGS=0	-1.0	-1.5		V

Marking : D1002

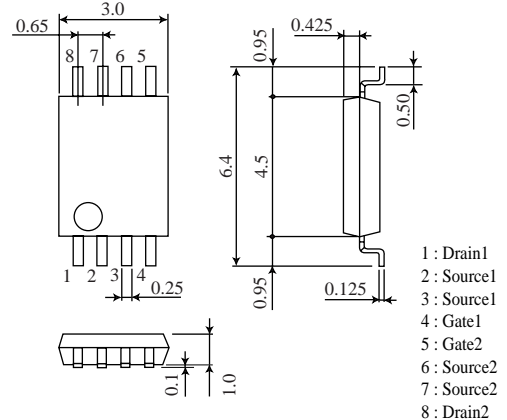
### Switching Time Test Circuit



### Electrical Connection



### Case Outline TSSOP8(unit:mm)



Specifications and information herein are subject to change without notice.

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